



BAS40-04

**SCHOTTKY DIODE 肖特基二極管(BAS40-04)**

■FEATURES 特點

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Power dissipation 耗散功率	$P_D(T_a=25^\circ\text{C})$	225	mW
Forward Current 正向電流	$I_F$	100	mA
Reverse Voltage 反向電壓	$V_R$	40	V
Junction and Storage Temperature 結溫和儲藏溫度	$T_J, T_{stg}$	-55to+150°C	

■DEVICE MARKING 打標

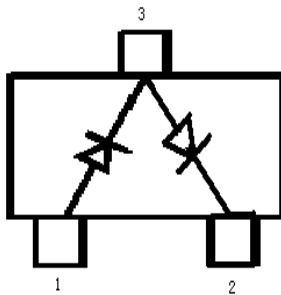
**BAS40-04=CB**

■ELECTRICAL CHARACTERISTICS 電特性

( $T_A=25^\circ\text{C}$  unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Max 最大值	Unit 單位
Reverse Breakdown Voltage 反向擊穿電壓 ( $I_R=10\mu\text{A}$ )	$V_{(BR)}$	40	—	V
Reverse Leakage Current 反向漏電流 ( $V_R=25\text{V}$ )	$I_R$	—	1	$\mu\text{A}$
Forward Voltage(Test Condition)正向電壓 $I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=40\text{mA}$	$V_F$	—	380 500 1000	mV
Diode Capacitance 二極體電容 ( $V_R=1\text{V}, f=1\text{MHz}$ )	$C_D$	—	5	pF
Reverse Recovery Time 反向恢復時間	$T_{rr}$	—	5	nS

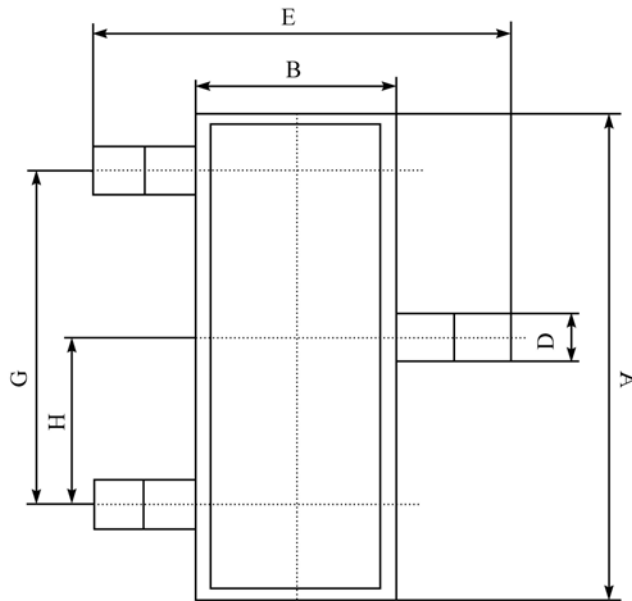
■SOT-23 内部结构



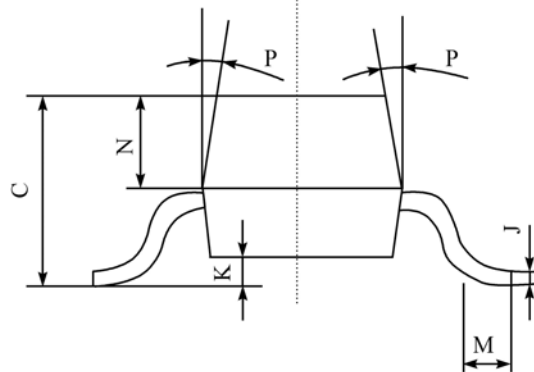


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■ DIMENSION 外形封裝尺寸



序號	數值及公差
A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.2
N	0.60±0.10
P	7±2°



This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website <http://www.takcheong.com>.

Although information in this datasheet has been carefully checked, no responsibility for the inaccuracies can be assumed by Tak Cheong. Please consult your nearest Tak Cheong's sales office for further assistance.

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